

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max $T_C = +25^\circ\text{C}$
30V	$4\text{m}\Omega @ V_{GS} = 10\text{V}$	75A
	$7\text{m}\Omega @ V_{GS} = 4.5\text{V}$	75A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Power Management Functions
- DC-DC Converters
- Backlighting

Features

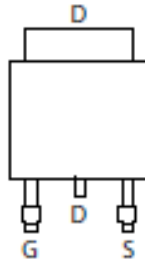
- Low On-Resistance
- Low Input Capacitance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

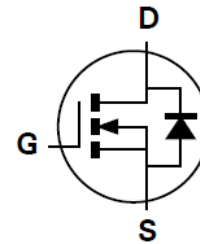
- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Matte Tin Finish.
- Solderable per MIL-STD-202, Method 208 [Ⓔ]
- Weight: 0.315 grams (Approximate)

NEW PRODUCT


Top View



Pin Out Top View



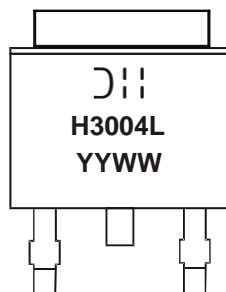
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH3004LK3-13	TO252	2500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



- D = Manufacturer's Marking
- H3004L = Product Type Marking Code
- YYWW = Date Code Marking
- YY = Last Two Digits of Year (ex: 15 = 2015)
- WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	+20 -16	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _C = +25°C T _C = +70°C	I _D	75 75	A
	Steady State	T _A = +25°C T _A = +70°C	I _D	21 17	A
Pulsed Drain Current (380μs Pulse, Duty Cycle=1%)			I _{DM}	160	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	3	A
Avalanche Current (Note 7) L=5mH			I _{AS}	10.7	A
Avalanche Energy (Note 7) L=5mH			E _{AS}	287	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P _D	1.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R _{θJA}	80	°C/W
Total Power Dissipation (Note 6)		P _D	3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	R _{θJA}	50	°C/W
Thermal Resistance, Junction to Case		R _{θJC}	1.4	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	-	-	10	μA	V _{DS} = 24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	100 -100	nA	V _{GS} = +20V, V _{DS} = 0V V _{GS} = -16V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1	-	3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	-	3.3	4	mΩ	V _{GS} = 10V, I _D = 20A
		-	5.5	7		V _{GS} = 4.5V, I _D = 7A
Diode Forward Voltage	V _{SD}	-	0.75	1	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{ISS}	-	2370	-	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{OSS}	-	1360	-	pF	
Reverse Transfer Capacitance	C _{RSS}	-	240	-	pF	
Gate Resistance	R _g	-	0.6	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	-	20	-	nC	V _{DS} = 15V, I _D = 20A
Total Gate Charge (V _{GS} = 10V)	Q _g	-	44	-	nC	
Gate-Source Charge	Q _{gs}	-	7	-	nC	
Gate-Drain Charge	Q _{gd}	-	8	-	nC	
Turn-On Delay Time	t _{D(ON)}	-	6.2	-	ns	V _{DD} = 15V, V _{GS} = 10V, R _L = 0.75Ω, R _G = 3Ω, I _D = 20A
Turn-On Rise Time	t _R	-	4.3	-	ns	
Turn-Off Delay Time	t _{D(OFF)}	-	21	-	ns	
Turn-Off Fall Time	t _F	-	8	-	ns	
Reverse Recovery Time	t _{RR}	-	25	-	ns	I _F = 15A, di/dt = 500A/μs
Reverse Recovery Charge	Q _{RR}	-	37	-	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

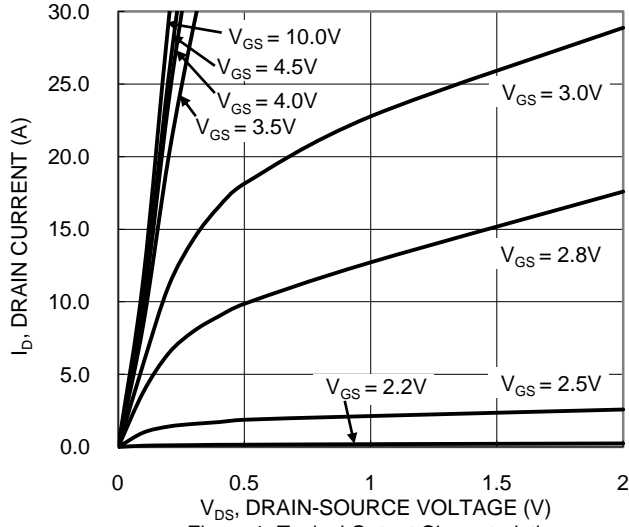


Figure 1. Typical Output Characteristic

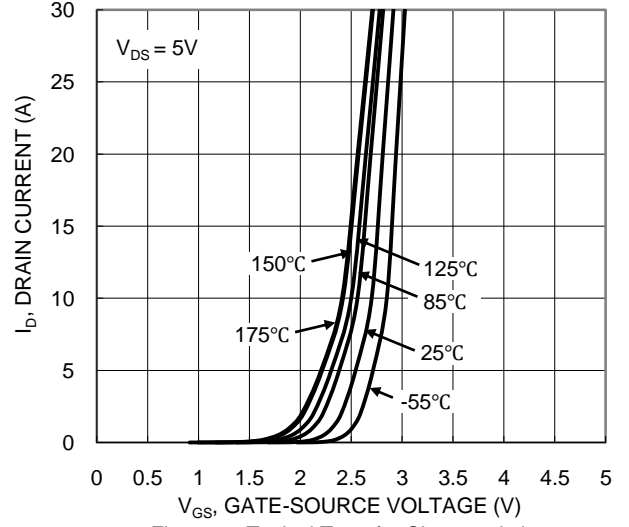


Figure 2. Typical Transfer Characteristic

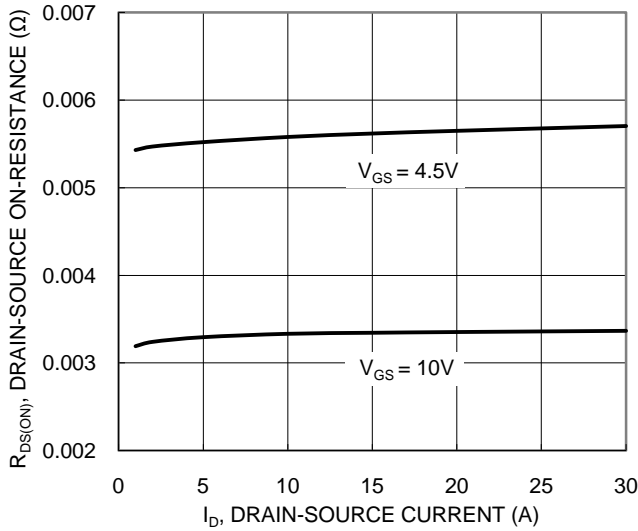


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

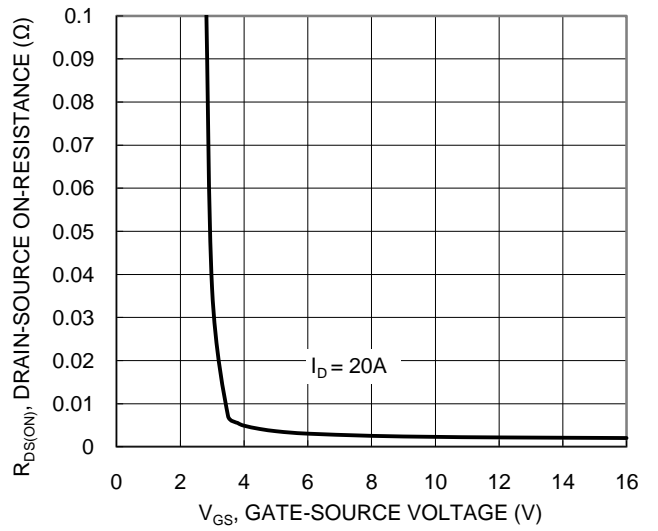


Figure 4. Typical Transfer Characteristic

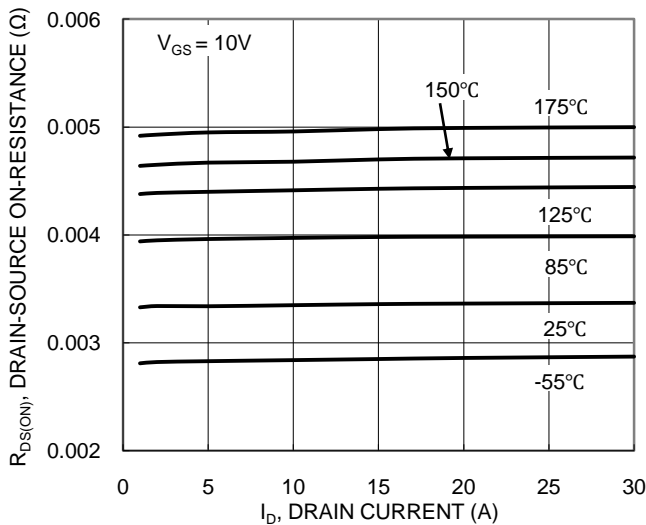


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

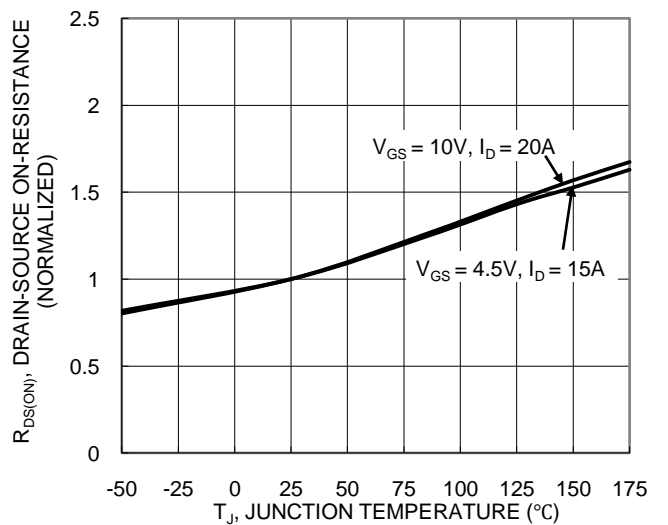


Figure 6. On-Resistance Variation with Junction Temperature

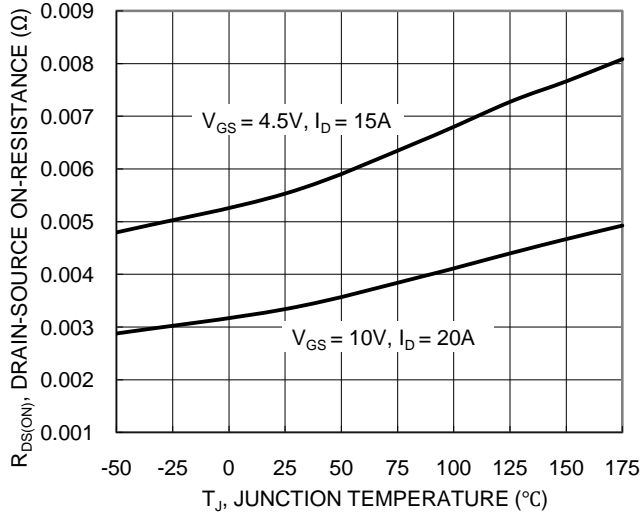


Figure 7. On-Resistance Variation with Junction Temperature

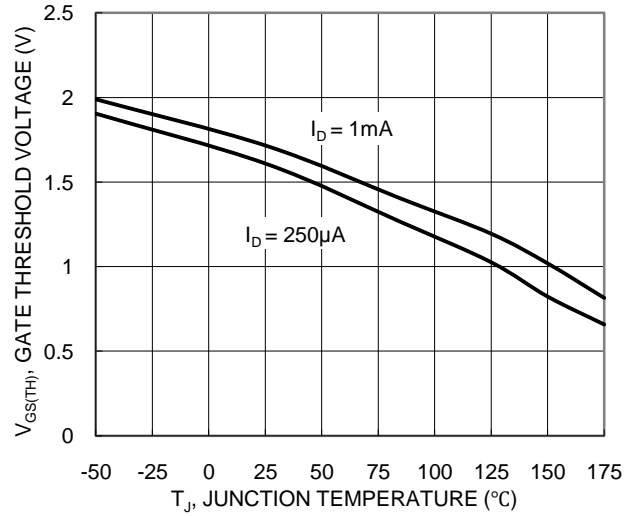


Figure 8. Gate Threshold Variation vs. Junction Temperature

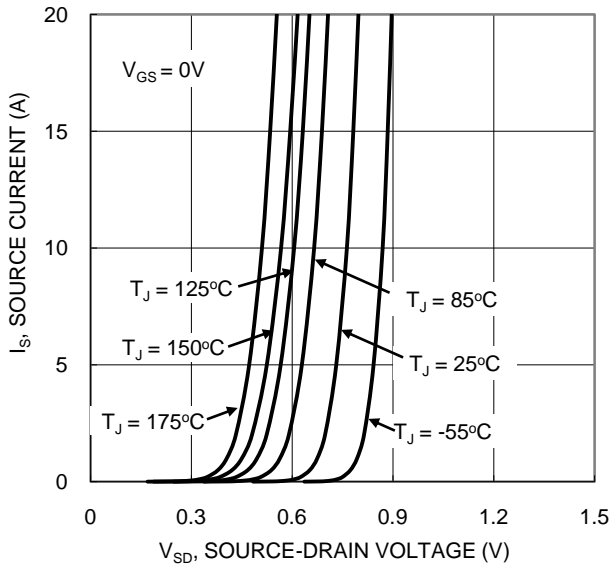


Figure 9. Diode Forward Voltage vs. Current

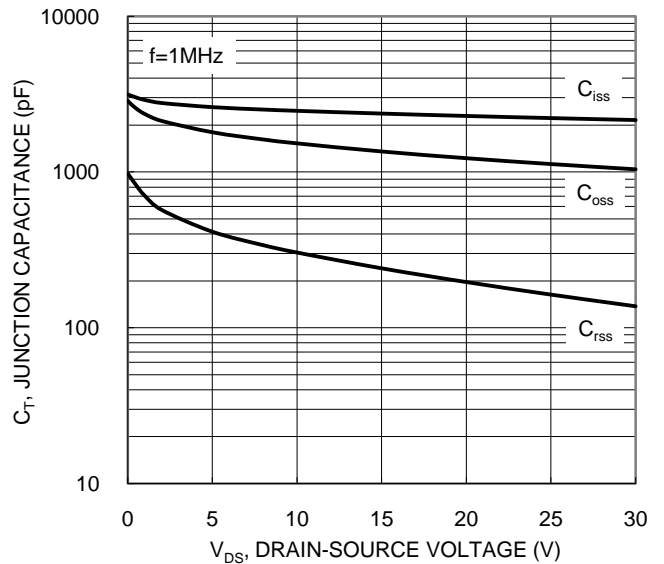


Figure 10. Typical Junction Capacitance

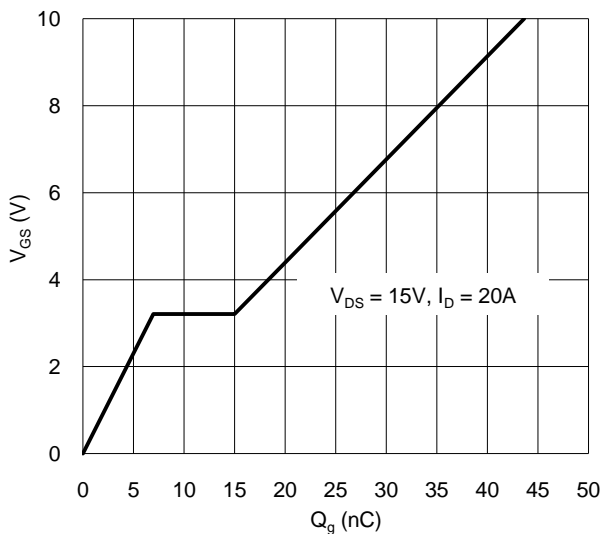


Figure 11. Gate Charge

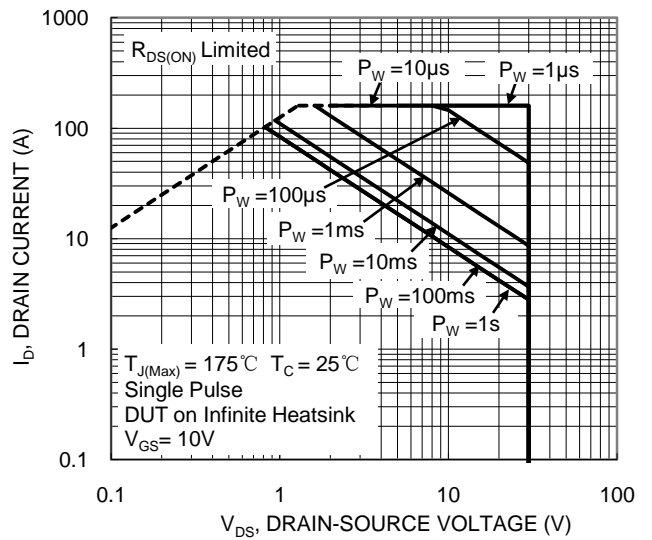


Figure 12. SOA, Safe Operation Area

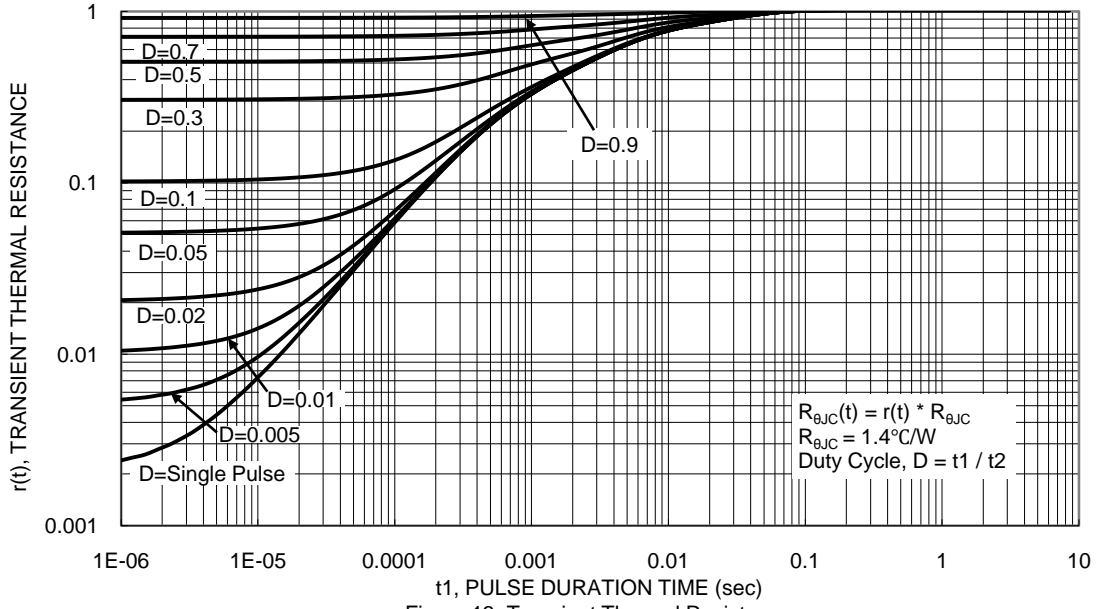
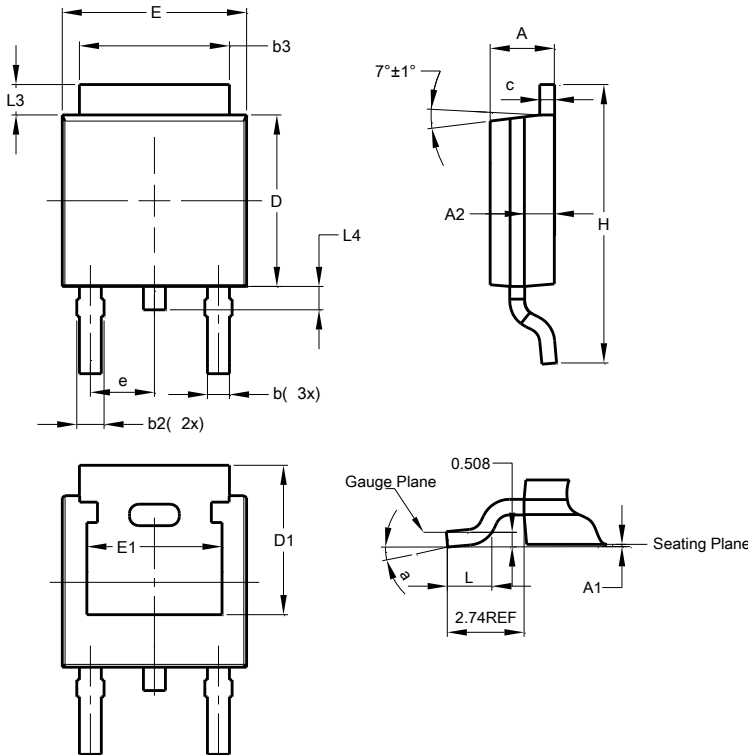


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

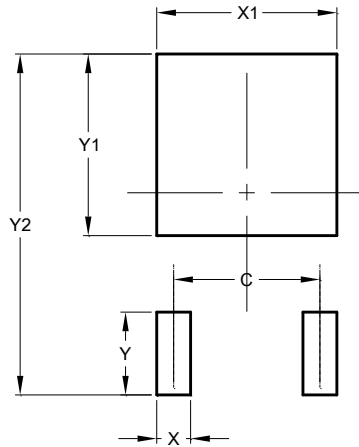
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

NEW PRODUCT

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